HSC285

Silicon Schottky Barrier Diode for High frequency detection

REJ03G0011-0100Z
Rev.1.00
Apr.16.2003

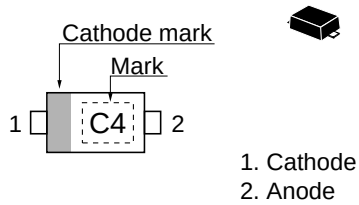
Features

- Low forward voltage, Low capacitance and High detection sensitivity.
- Ultra small Flat Package (UFP) is suitable for surface mount design.

Ordering Information

Type No.	Laser Mark	Package Code
HSC285	C4	UFP

Pin Arrangement



1. Cathode
2. Anode

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	V_R	2	V
Average rectified current	I_O	5	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	–55 to +125	°C

Electrical Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_{F1}	—	—	0.15	V	I_F = 0.1 mA
	V_{F2}	—	—	0.27		I_F = 1 mA
Capacitance	C	—	0.3	—	pF	V_R = 1 V, f = 1 MHz
ESD-Capability *[1]	—	10	—	—	V	C = 200 pF, R_L = 0 Ω, Both forward and reverse direction 1 pulse.

Note: 1. Failure criterion ; I_R > 100 μA at V_R = 0.5 V

Main Characteristic

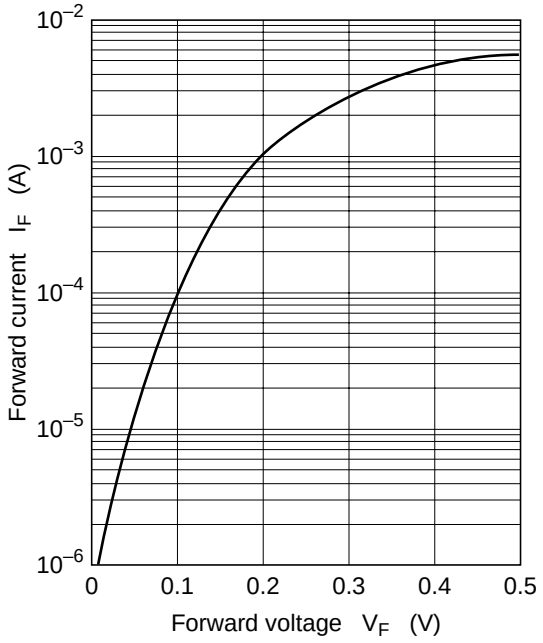


Fig.1 Forward current vs. Forward voltage

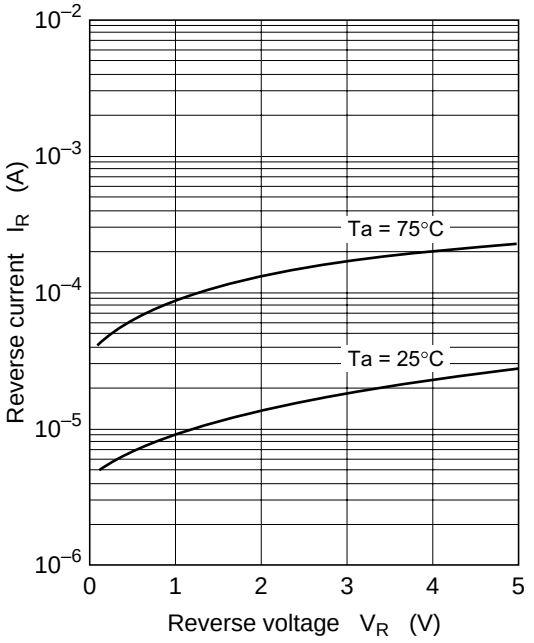


Fig.2 Reverse current vs. Reverse voltage

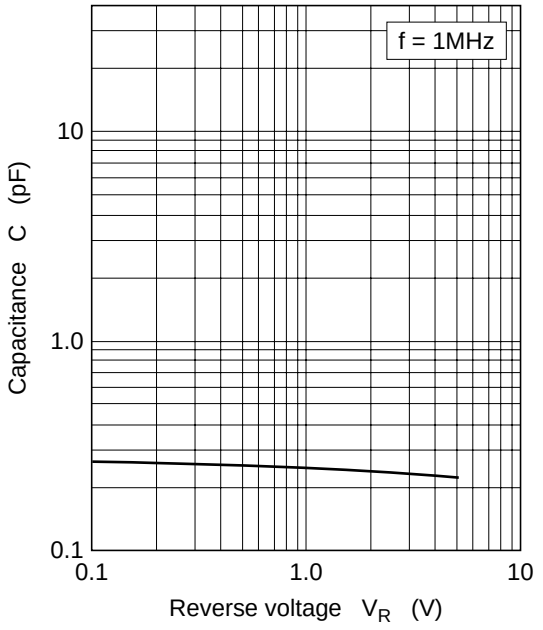
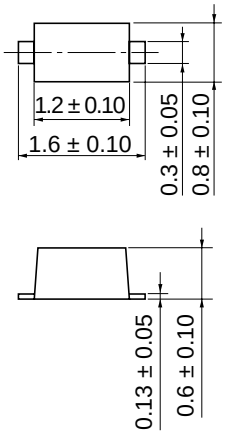


Fig.3 Capacitance vs. Reverse voltage

Package Dimensions

As of January, 2003
Unit: mm



Package Code	UFP
JEDEC	—
JEITA	Conforms
Mass (reference value)	0.0016 g

Renesas Technology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

http://www.renesas.com

Colophon 0.0